

Keynote Speaker

Martin Kuball (Univ. of Bristol),
“Unleashing the power of diamond – Heterogenous integrations”

Invited Speakers (tentative)

- 1) **Keisuke Shinohara**, Teledyne Scientific & Imaging, *“Multi 2DEG Channel BRIDGE HEMT Technology for Millimeter-Wave Power Amplifier and RF Switch Applications”*
- 2) **Edward Chang**, National Chiao Tung Univ., *“A High Current E-mode GaN HEMT with Thin Barrier Layer”*
- 3) **Dinesh Ramanathan**, NEXGEN, *“Reinventing Power Electronics: NexGen Power Systems with NexGen Vertical GaN™”*
- 4) **Rongming Chu**, Pennsylvania State Univ., *“Opportunities and Challenges of GaN Super-Heterojunction (Tentative)”*
- 5) **Uttam Singiset**, Univ. at Buffalo, *“Gallium oxides lateral devices: kV power transistor to high power switched mode RF amplifiers”*
- 6) **Heiji Watanabe**, Osaka Univ., *“Interface science and engineering for GaN-based MOS devices”*
- 7) **Tsunenobu Kimoto**, Kyoto Univ., *“High Mobility in SiC MOSFETs with Heavily-Doped p-Bodie”*
- 8) **Xufang Zhang**, Kanazawa Univ., *“Recent Progress in Electrical Characterization of Al₂O₃/Diamond Interface”*
- 9) **Makoto Kasu**, Saga Univ., *“Diamond 2-Inch-Wafer Growth and 875-MW/cm² Power FET”*
- 10) **Colombo Bolognesi**, ETH Zurich, *“InP/GaAsSb DHBTs: Historical Evolution, Device Physics, and State-of-the-Art Performance”*
- 11) **Takuya Hoshi**, NTT, *“Recent Progress in Metal-Organic Vapor Phase Epitaxy of InP-based Ultrahigh-Speed Transistors”*
- 12) **Michael Feiginov**, Technical Univ. of Vienna, *“Sub-THz and THz Double-Resonant-Tunnelling-Diode Patch-Antenna Oscillators”*

13) **Eduardo M Chumbes**, Raytheon Missiles & Defense, "*ScAlN/GaN Heterojunction Field Effect Transistors for Ultra-high power and efficient RF Power Amplifiers*"

14) **Joachim Würfl**, Ferdinand-Braun-Institut, "*AlN based devices for new power electronic switches and mm-wave power MMICs*"

15) **Hyeon-Bhin Jo**, Kyungpook National Univ., "*In_{0.53}Ga_{0.47}As Multi-Bridge Channel Field-Effect-Transistors for future CMOS applications*"

16) **Yoshio Honda**, Nagoya Univ., "*Correlation between Dislocation and Reverse Leakage Current in GaN pn Junction*"

17) **Manabu Arai**, Nagoya Univ.